ABSTRACT OF THE DISCLOSURE

This invention comprises methods of forming patterned photoresist layers over semiconductor substrates. In one implementation, a semiconductor substrate is provided. An antireflective coating is formed over the semiconductor substrate. The antireflective coating has an outer surface. The outer surface is treated with a basic fluid. A positive photoresist is applied onto the outer surface which has been treated with the basic treating fluid. The positive photoresist is patterned and developed effective to form a patterned photoresist layer having increased footing at a base region of said layer than would otherwise occur in the absence of said treating the outer surface. Other aspects and implementations are contemplated.

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